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(54) **Title**: SEMICONDUCTOR PROCESSING

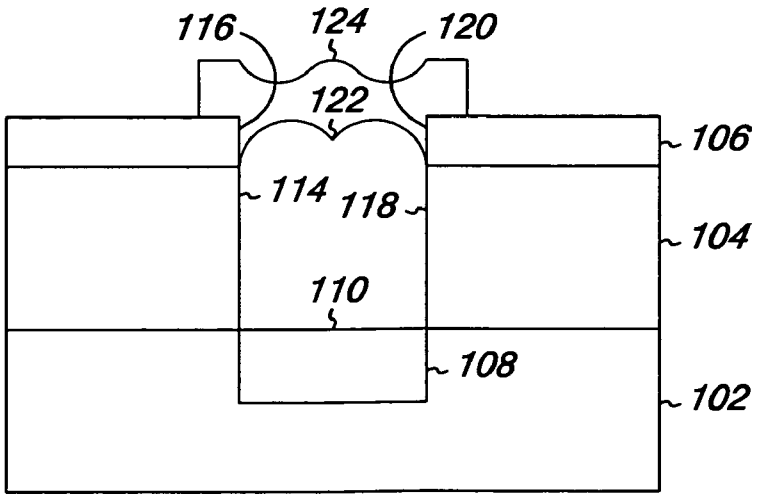


Fig. 1E

(57) **Abstract**: Devices, methods, and systems for semiconductor processing are described herein. A number of method embodiments of semiconductor processing can include forming a silicon layer on a structure, forming an opening through the silicon layer and into the structure, and selectively forming a resistance variable material in the opening such that the resistance variable material does not form on the silicon layer.

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